



ELEC-336 PROJECT

Differential Amplifier Design

Group Members :	Muhammed Said Modalı
Numbers :	210102002071

1. Objective

The purpose of **differential pair design** in electronics is to eliminate noise and amplify the signal by applying two signals with a 180-degree phase difference on both sides. This results in a higher quality and stronger signal.

Its application areas include sound, video, and internet usage.

The operating principle is shown in Figure 1.

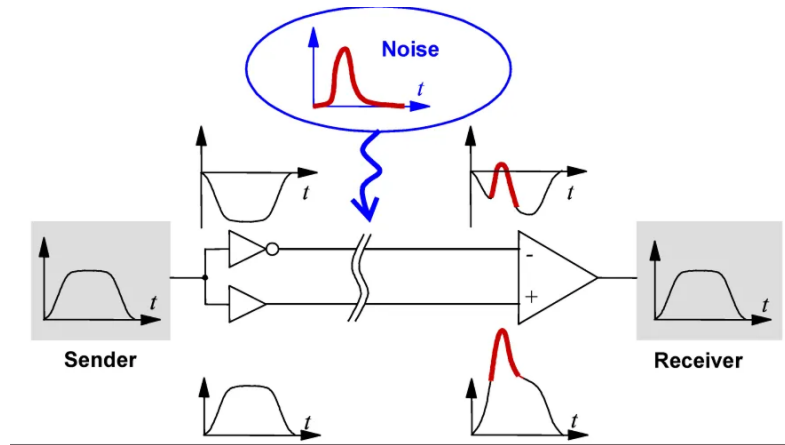


Figure 1.

2. Circuit Design

As required in the project, the LTSpice program has been used.

As required in the project, the PMOS and NMOS have been included in LTSpice. These two MOSFETs are manufactured using 180nm technology.

According to the code, the values of μ_{Cox} and V_{th} have been determined.

	PMOS	NMOS
V_{th}	0.4 v	0.4 v
μ_{Cox} (mobility multiplied by oxide capacitance)	$3 \times 10^{-4} \text{ A/V}^2$	$3.5 \times 10^{-2} \text{ A/V}^2$

The schematic design essentially consists of two PMOS transistors on the top and two main NMOS transistors on the bottom. The upper part represents the active load section. Below the NMOS transistors, a tail current source for biasing is added. The DC supply is set to $V_{DD} = 1.8\text{V}$, and the signals are 180 degrees out of phase with an amplitude of 0.1mVpp (0.05mVp) and a frequency of 10kHz. The circuit is shown in Figure 2 in LTSpice.

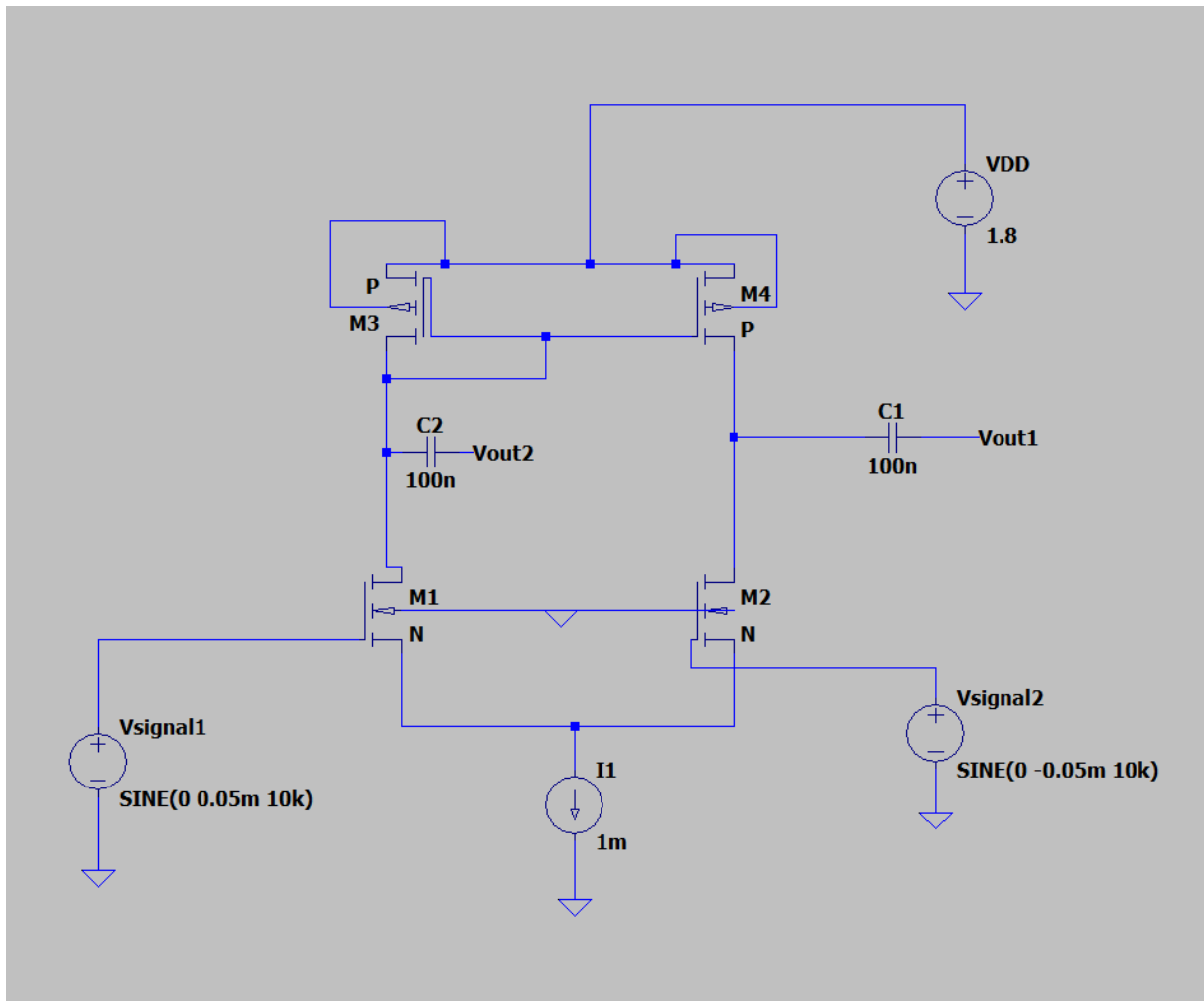


Figure 2.

The W/L ratios of the MOSFETs :

	W	L	W/L
PMOS	50u	1u	50
NMOS	900u	1u	900

Monolithic MOSFET - M3

Model Name: P OK Cancel

Length(L): 1u

Width(W): 50u

Drain Area(AD):

Source Area(AS):

Drain Perimeter(PD):

Source Perimeter(PS):

No. Parallel Devices(M):

P I=1u w=50u

Monolithic MOSFET - M1

Model Name: N OK Cancel

Length(L): 1u

Width(W): 900u

Drain Area(AD):

Source Area(AS):

Drain Perimeter(PD):

Source Perimeter(PS):

No. Parallel Devices(M):

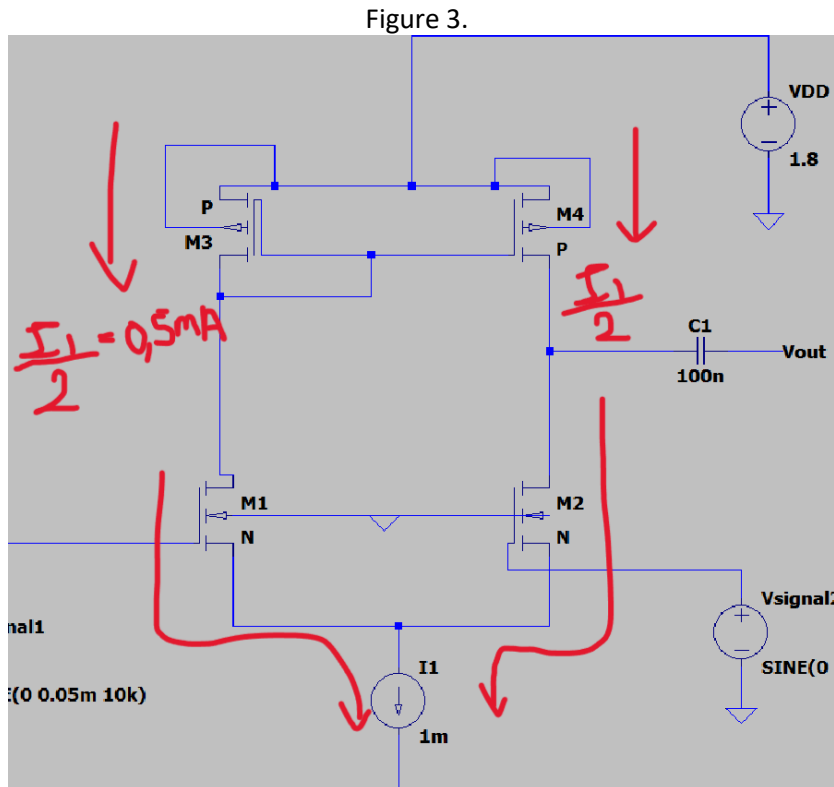
N I=1u w=900u

3. Simulation

3.1 DC ANALYSIS

Before starting the simulation, it is necessary to analytically calculate and test whether the transistor is operating in the saturation region.

As shown in Figure 3. , the I_{sd} current should be 0.5mA.



Then, the V_{sg} current can be found from the equation of the PMOS operating in the saturation mode.

$$I_{SD} = \frac{1}{2} \mu C_{ox} \left(\frac{W}{L} \right) (V_{sg} - V_{th})^2$$

$$0.0005 = \frac{1}{2} 0.015 \times 130 (V_{sg} - 0.4)^2$$

$$V_{SG} = 0.64v$$

And, it must be $V_{SG}(0.64v) > v_{th}(0.4v)$. Therefore, it is correct for saturation mode and others.

The accuracy of the values has been tested through simulation in LTspice On Figure 3.1.

```

--- Operating Point ---

V(n002) :      0.623818      voltage
V(n001) :      1.8          voltage
V(n003) :      0.623818      voltage
V(n004) :      0            voltage
V(n006) :     -0.526793      voltage
V(n005) :      0            voltage
V(vout) :     6.23818e-008    voltage
Id(M2) :      0.000492992     device_current
Ig(M2) :      0              device_current
Ib(M2) :      7.00759e-006    device_current
Is(M2) :     -0.0005          device_current
Id(M1) :      0.000492992     device_current
Ig(M1) :      0              device_current
Ib(M1) :      7.00759e-006    device_current
Is(M1) :     -0.0005          device_current
Id(M4) :      0.000492992     device_current
Ig(M4) :     -0              device_current
Ib(M4) :      1.18618e-012    device_current
Is(M4) :     -0.000492992     device_current
Id(M3) :     -0.000492992     device_current
Ig(M3) :     -0              device_current
Ib(M3) :      1.18618e-012    device_current
Is(M3) :      0.000492992     device_current
I(C1) :      -6.23818e-020    device_current
I(I1) :      0.001            device_current
I(Vsignal1) : 0              device_current
I(Vsignal2) : 0              device_current
I(Vdd) :     -0.000985985     device_current

```

Figure 3.1

3.2 AC ANALYSIS

For the AC analysis, the input signal is shown in Figure 3.2.

$$(0.01\text{m(vpp)} = 0.05\text{m(vp)}) = (50\text{u(vp)})$$

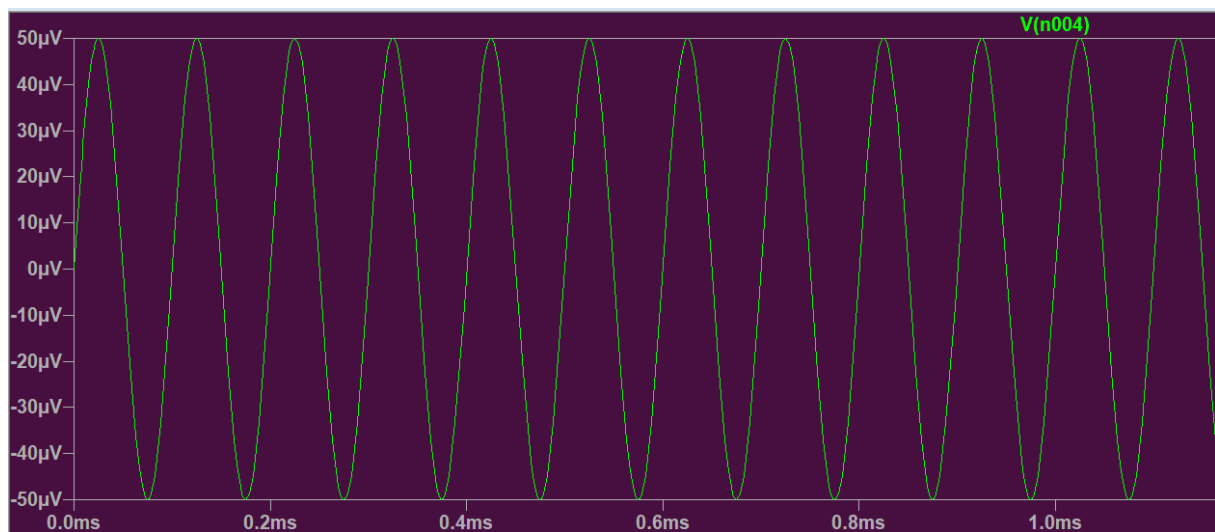


Figure 3.2($V(n004) = \text{vsignal1}$)

Later, the Vout1 signal is shown in Figure 3.3.

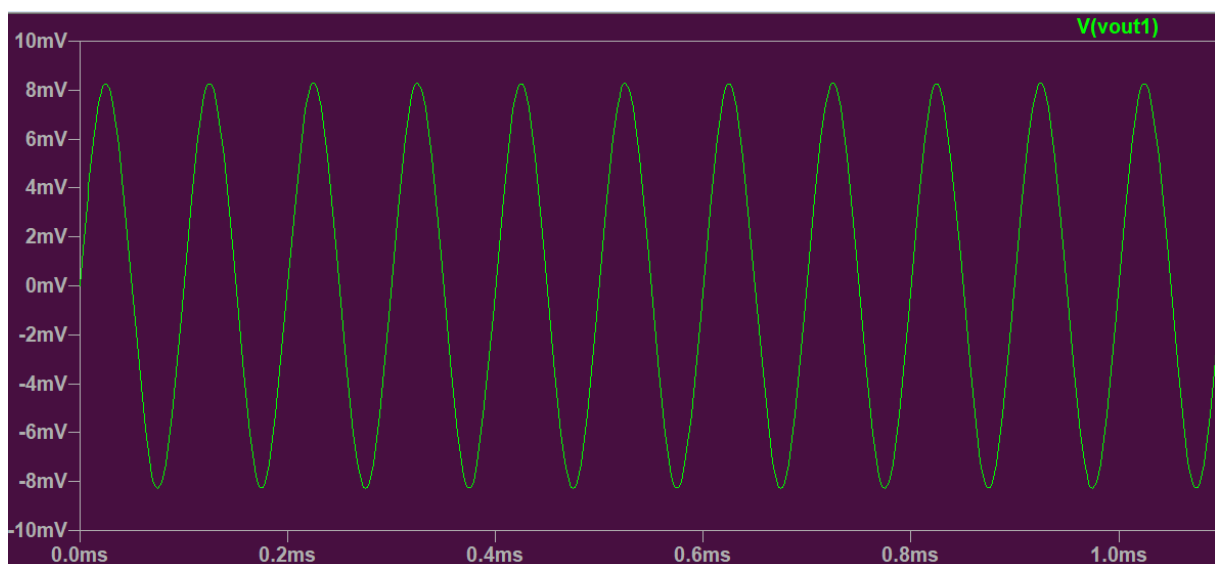
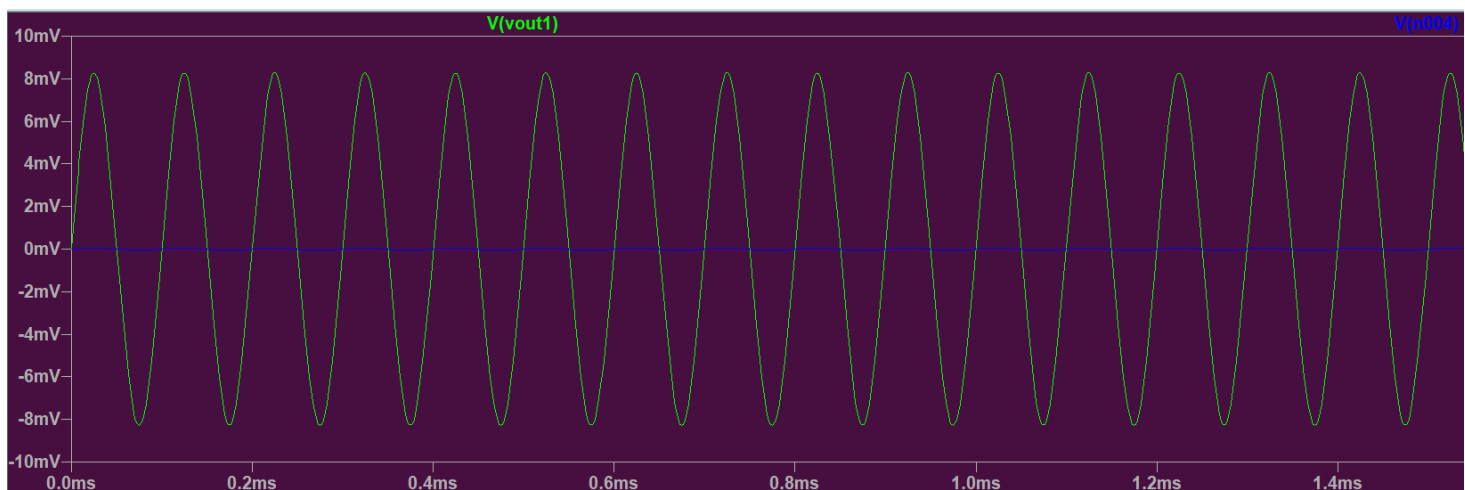


Figure 3.3

Totally (Figure 3.4) :



The differential gain is given with a phase difference, while the common mode gain is given without a phase difference and is applied to the common signal.

Differential Gain (A_d) :

The parameters :

Difference between vout1 and vout2 is required (Figure 3.5):

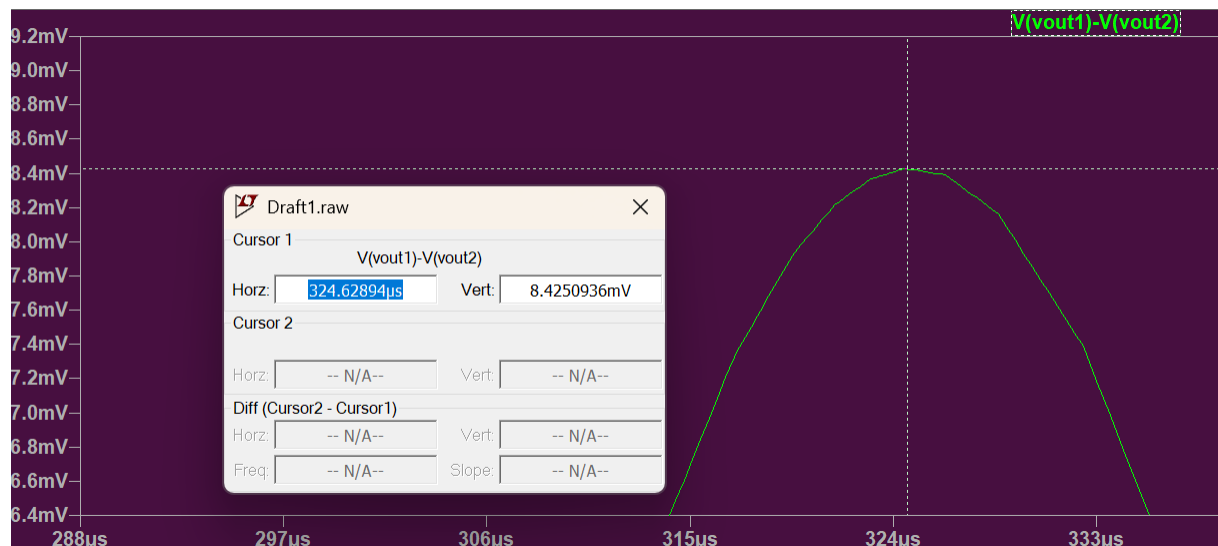


Figure 3.5

Difference between vsignal1 and vsignal2 is required (Figure 3.6):

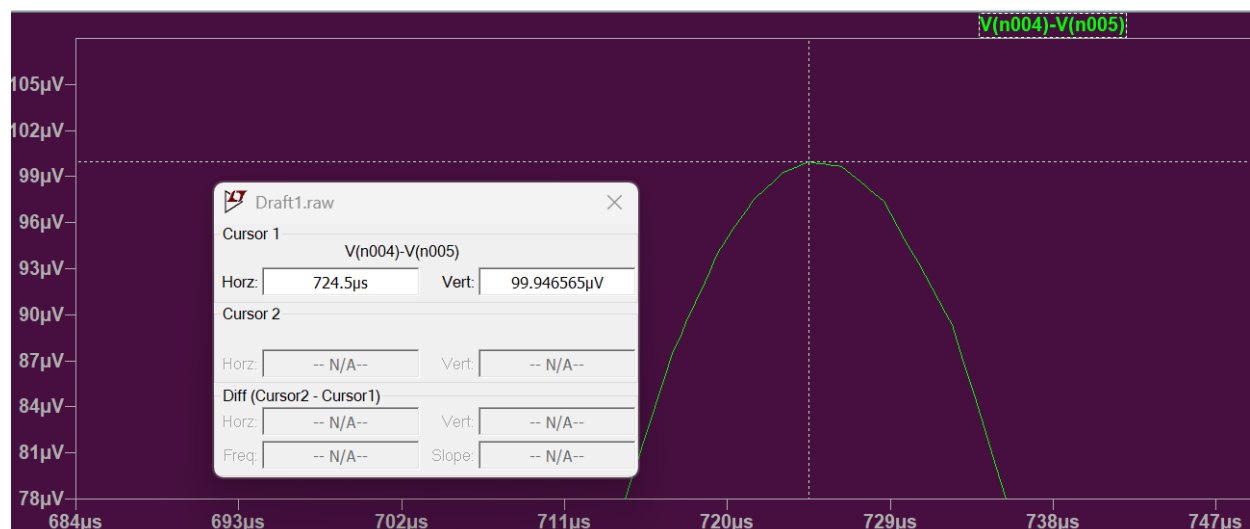


Figure 3.6

Calculating (A_d) :

$$A_d = \frac{\Delta V_{out}}{\Delta V_{in}} = \frac{V_{out1} - V_{out2}}{V_{signal1} - V_{signal2}} = \frac{8.42\text{mv}}{100\text{uv}} = 84.2(v/v)$$

Common-Mode Gain (A_{cm}) :

To calculate the common-mode gain, the 180-degree phase difference between the input sources is removed, and then the average of V_{out1} V_{out1} and V_{out2} V_{out2} is taken. Similarly, the average of $V_{signal1}$ $V_{signal1}$ and $V_{signal2}$ $V_{signal2}$ is computed. The ratio of the output average to the input average gives the common-mode gain.

The parameters :

For v_{out} , the average of v_{out1} and v_{out2} is taken (Figure 3.6) :

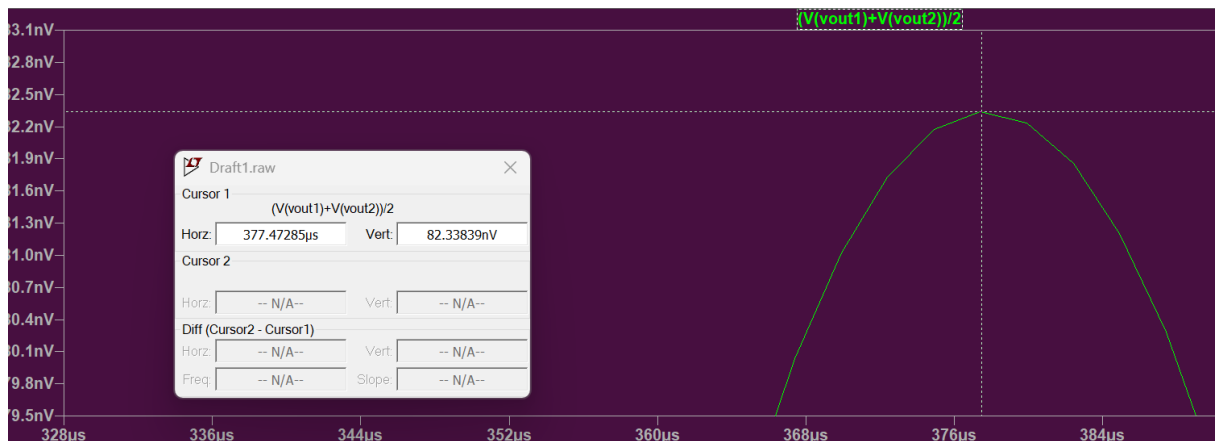


Figure 3.6

For v_{in} , the average of $v_{signal1}$ and $v_{signal2}$ is taken (Figure 3.7) :

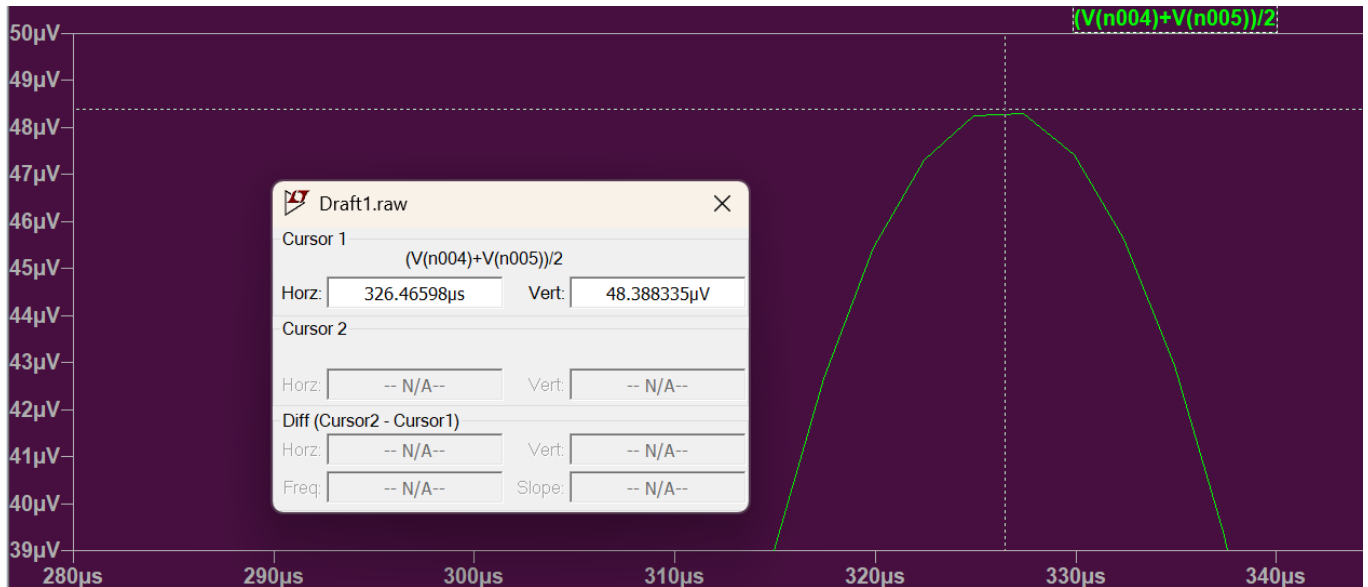


Figure 3.7

Calculating (A_{cm}) :

$$A_{cm} = \frac{V_{out}(\text{common})}{V_{in}(\text{common})} = \frac{82.34\text{nv}}{48.39\text{uv}} = 0.0017(v/v)$$

Calculating (CMRR) :

CMRR (Common-Mode Rejection Ratio) is a performance parameter that measures the ability of a differential amplifier to suppress common-mode signals

$$\text{CMRR} = 20 \log \left(\frac{A_d}{A_{cm}} \right) = \left(\frac{84.2}{0.0017} \right) = 93.9\text{db}$$

Calculation and observing of 3dB Bandwith :

$$A_d = 84.2(v/v)$$

$$A_d(db) = 20 \log(A_d) = 20 \log(84.2) = 38.5(db) \text{ (Figure 3.8 and 3.9)}$$

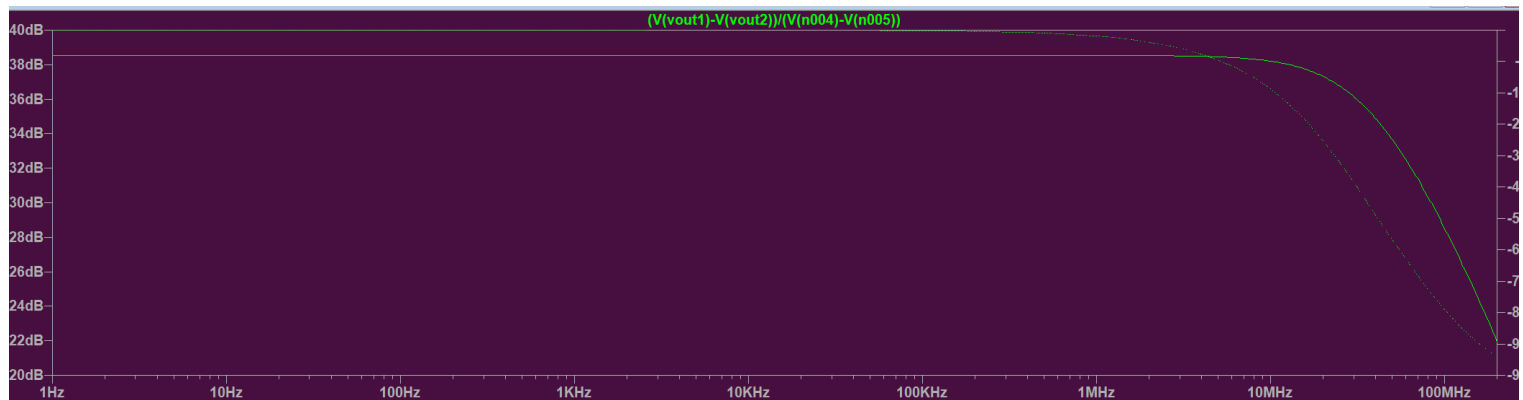


Figure 3.8

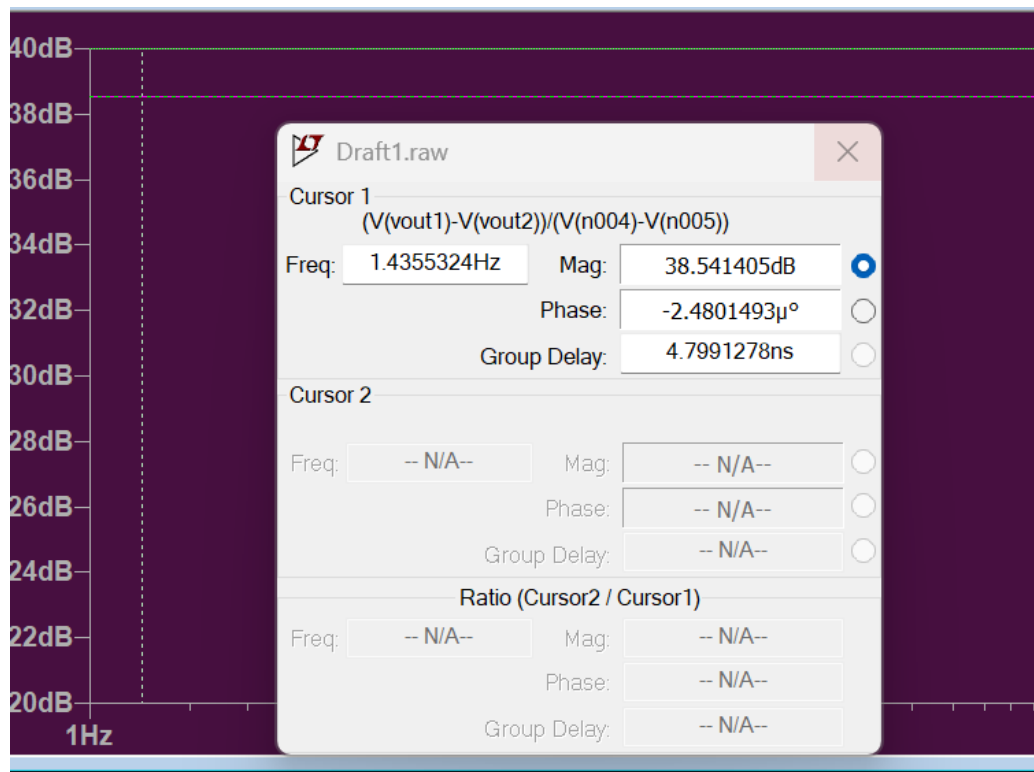


Figure 3.9

As shown in Figures 3.8 and 3.9, the AdA_dAd gain is 38.5 dB. To find the 3 dB bandwidth, the frequency at which the gain shows 35.5 dB (which is also 0.7 times the maximum gain) is shown in Figure 3.10

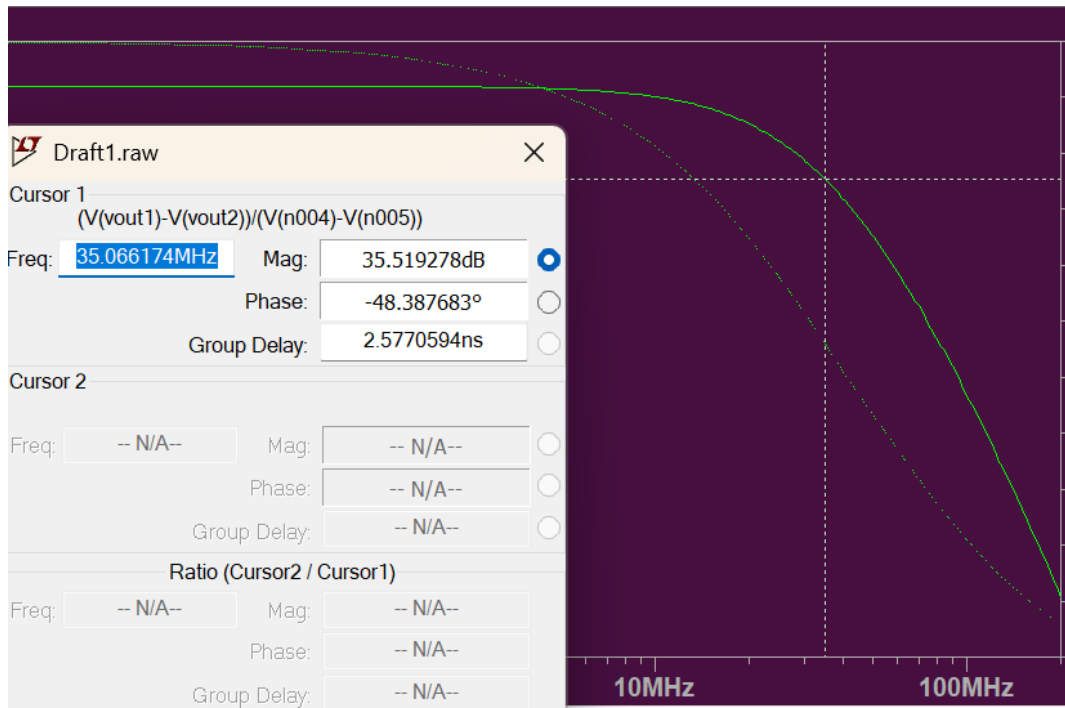


Figure 3.10

The 3 dB bandwidth = 35 MHz.

Unity gain:

it represents a gain of 1, or the 0 dB point (Figure 3.11 and 3.12)

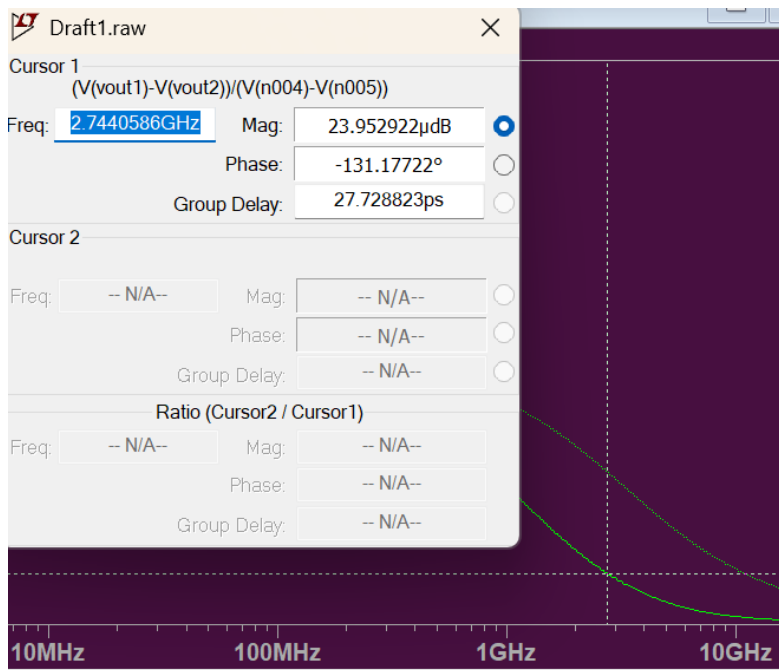


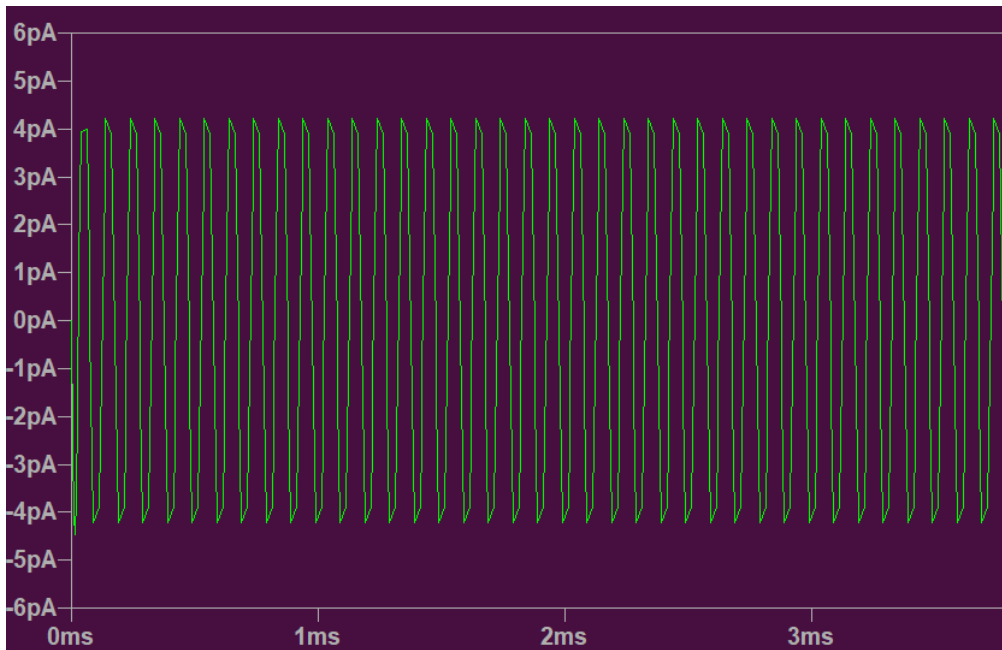
Figure 3.11



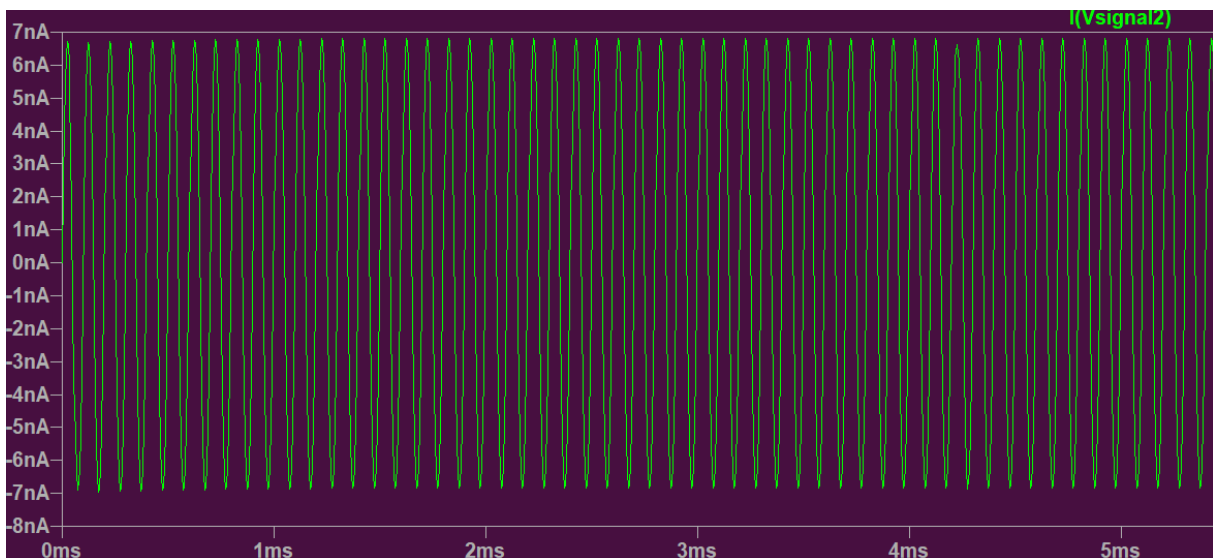
Figure 3.12

unity gain = 2.74Ghz.

Calculating input empedance and output empedance :



$$Z_{in} = \left(\frac{V_{signal}}{I_{in}} \right) = \frac{0.05m(vp)}{4pA} = 12.5M\Omega$$



$$Z_{out} = \left(\frac{V_{signal}}{I_{out}} \right) = \frac{0.05m(vp)}{7nA} = 7.1k\Omega$$

When calculating Z_{in} and Z_{out} , Thevenin's theorem is applied, and test voltages V_{test} are applied. Then, the current is measured and the ratio is calculated.

Transient Analysis

The input starts at 0.05 mVp and the amplitude is increased step by step. The resulting outputs are presented in Table 2.

	vout	Wave type
0.05m(vp)	8m(vp)	sinusoidal
0.1m(vp)	16m(vp)	sinusoidal
1m(vp)	160m(vp)	sinusoidal
5m(vp)	700m(vp)	sinusoidal
10m(vp)	600m(vp)	Sinusoidal(but voltage drift)

Table2

As seen from the values, for 10mV and beyond, the amplifier will distort both the gain and the waveform. A maximum of 10mV should be applied to the input.

4. Design Optimization

In the project, a gain of $A_d > 80$ v/v is required. Since $A_d = 84.2$, it is clear that **84.2** >> **80**, and the desired value is achieved.

CMRR > 60dB is required. Since **93.9** >> **60dB**, the desired value is achieved.

The W/L ratio of the MOSFETs, especially the NMOS transistors, was initially high. Later, the W/L ratio was reduced to 100, and the tail current was also reduced to 0.1, which led to the MOSFETs drawing less current. As a result, the MOSFETs consumed less power, and at the same time, the gain increased.

	W	L	W/L
PMOS	50u	1u	50
NMOS	100u	1u	100

Table 3

Calculating Gain :

Figures 4.0, 4.1, and 4.2 show the voltage values obtained for calculating the Ad gain.

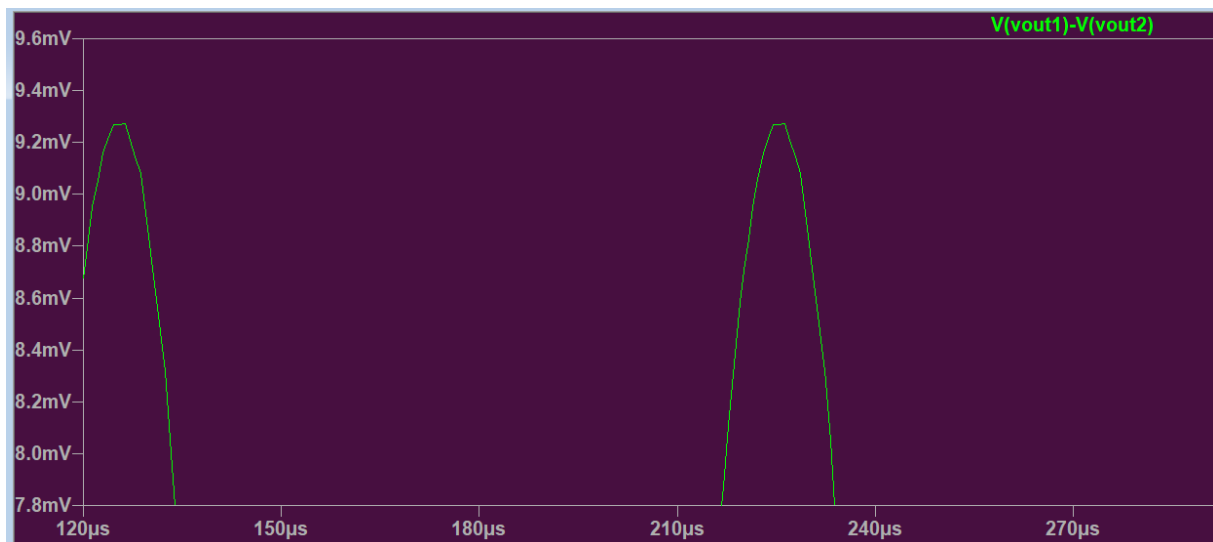


Figure 4.0

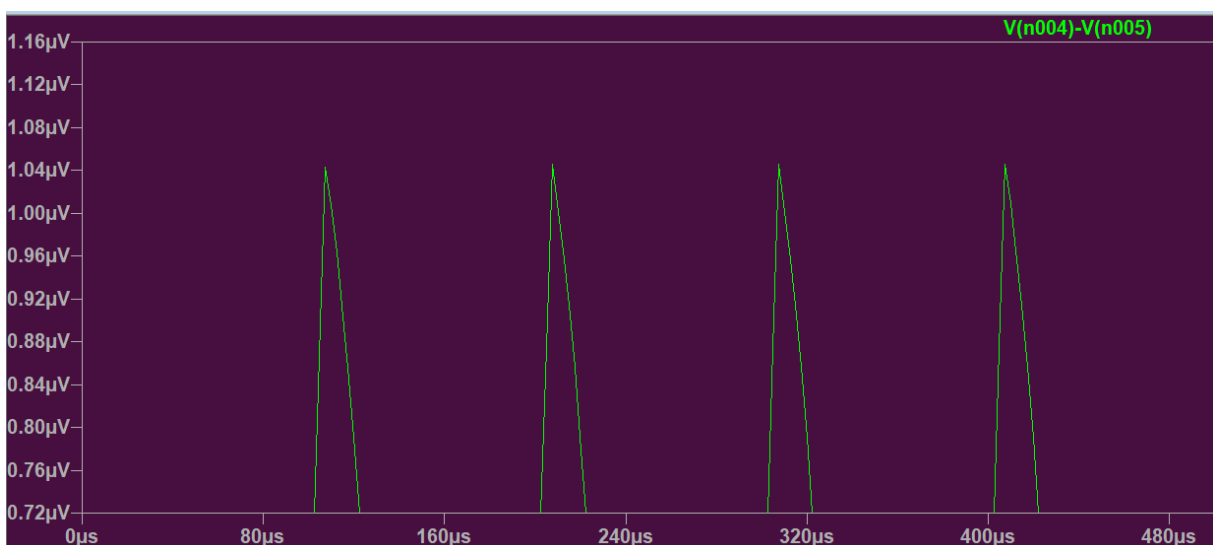


Figure 4.1

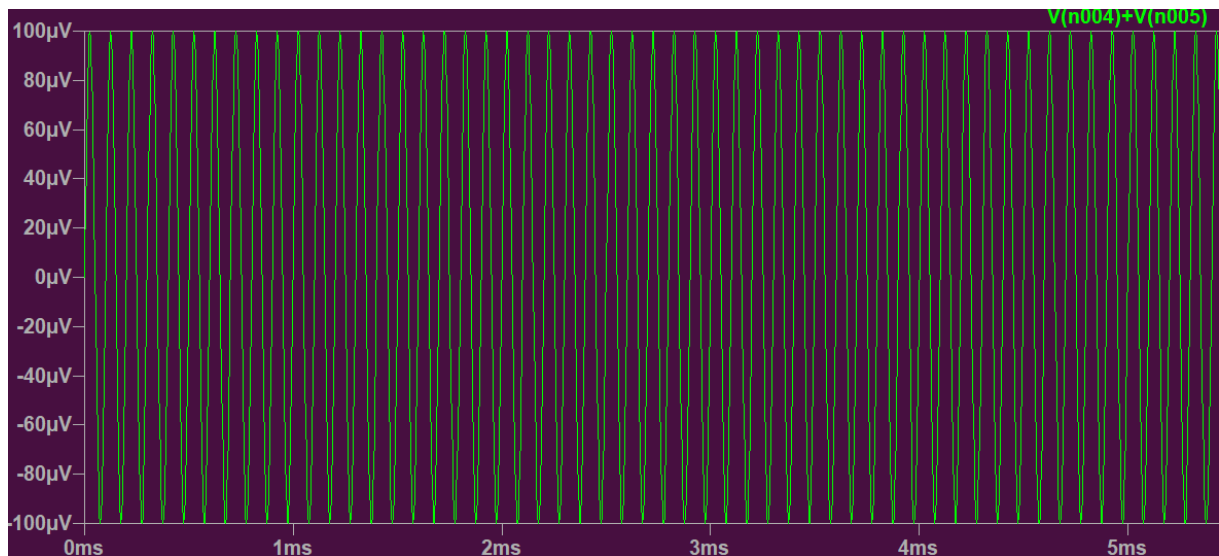


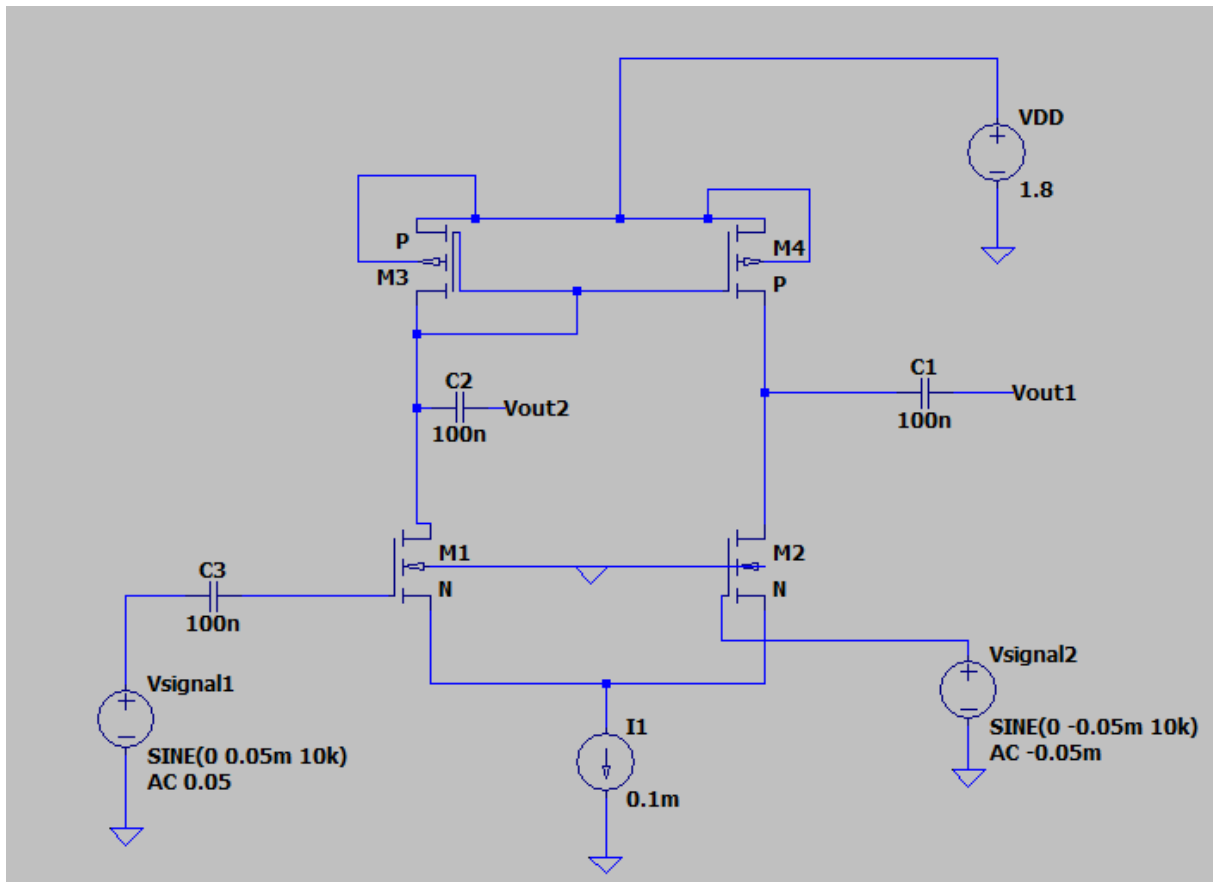
Figure 4.2

$$A_d = \frac{\Delta V_{out}}{\Delta V_{in}} = \frac{V_{out1} - V_{out2}}{V_{signal1} - V_{signal2}} = \frac{9.3\text{mv}}{100\text{uv}} = 93(v/v)$$

$$A_{cm} = \frac{V_{out(common)}}{V_{in(common)}} = \frac{40\text{nv}}{0.05\text{mv}} = 0.0008(v/v)$$

$$\text{CMRR} = 20 \log \left(\frac{A_d}{A_{cm}} \right) = \left(\frac{93}{0.0008} \right) = 101\text{db}$$

End of the design (Figure 4.3):



Figure(4.3)

Conclusion :

The final version of the circuit is shown in Figure 4.3. The W/L ratios have been reduced, and the tail current has been set to 0.1mA, resulting in an increase in differential gain and CMRR. The main reason for these changes was to achieve power optimization, and thus, the design has been completed.

The general assessment of this project is to design a basic differential op-amp in LTSpice, gain expressions, monitoring of graphs, and gaining fundamental knowledge about power optimization.

REFERENCES:

- [1]: https://en.wikipedia.org/wiki/Differential_signalling
- [2]: <https://www.youtube.com/watch?v=ErpKbG7HCG0&t=144s>
- [3]: https://www.youtube.com/watch?v=_pvlk_SlyDo
- [4]: https://www.youtube.com/watch?v=_qKFQ1H_zOI&t=68s
- [5]: <https://www.youtube.com/watch?v=KvrNSPQ58vA&t=216s>
- [6]: <https://www.youtube.com/watch?v=j4OS3zOqdJg&t=367s>